



2N7002

Power MOSFET

N-CHANNEL ENHANCEMENT MODE

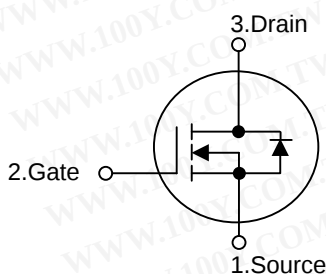
DESCRIPTION

The UTC **2N7002** has been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. It can be used in most applications requiring up to 400mA DC and can deliver pulsed currents up to 2A. The product is particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications

FEATURES

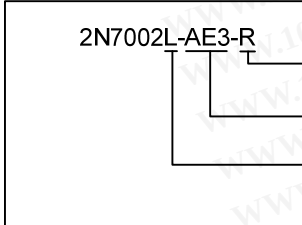
- * High density cell design for low $R_{DS(ON)}$.
- * Voltage controlled small signal switch
- * Rugged and reliable
- * High saturation current capability

SYMBOL

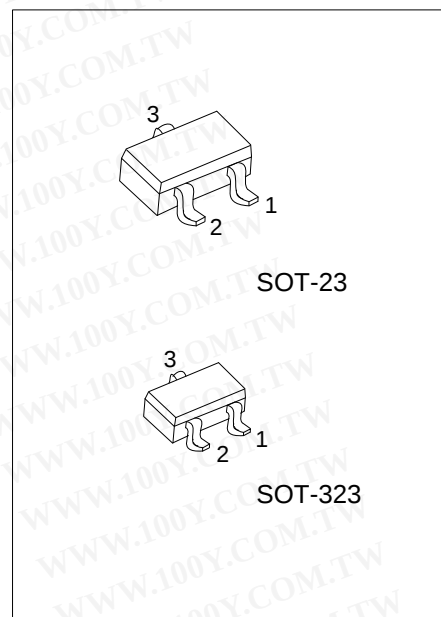
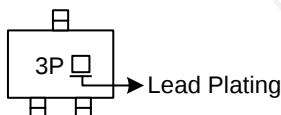


ORDERING INFORMATION

Ordering Number			Package	Pin Assignment			Packing
Normal	Lead Free Plating	Halogen-Free		1	2	3	
2N7002-AE3-R	2N7002L-AE3-R	2N7002G-AE3-R	SOT-23	S	G	D	Tape Reel
2N7002-AL3-R	2N7002L-AL3-R	2N7002G-AL3-R	SOT-323	S	G	D	Tape Reel

	(1) Packing Type (2) Package Type (3) Lead Plating	(1) R: Tape Reel (2) AE3: SOT-23, AL3: SOT-323 (3) G: Halogen Free, L: Lead Free Plating, Blank: Pb/Sn
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MARKING



Lead-free: 2N7002L

Halogen-free: 2N7002G

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-54151736
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C unless otherwise noted.)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DS}	60	V
Drain-Gate Voltage ($R_{GS} \leq 1M\Omega$)	V_{DGR}	60	V
Gate Source Voltage	V_{GSS}	± 20	V
		± 40	
Drain Current	I_D	300	mA
		800	
Power Dissipation Derated Above 25°C	P_D	200 1.6	mW mW/°C
Junction Temperature	T_J	+ 150	°C
Storage Temperature	T_{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	625	°C/W

■ ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =10μA	60			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	μA
Gate-Source Leakage Current	I _{GSSF}	V _{GS} =20V, V _{DS} =0V			100	nA
	I _{GSSR}	V _{GS} =-20V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS (Note)						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D =250μA	1	2.1	2.5	V
Drain-Source On-Voltage	V _{DS (ON)}	V _{GS} = 10V, I _D =500mA		0.6	3.75	V
		V _{GS} = 5.0V, I _D =50mA		0.09	1.5	
On-State Drain Current	I _{D(ON)}	V _{GS} =10V, V _{DS} ≥2V _{DS(ON)}	500	2700		mA
Static Drain-Source On-Resistance	R _{DS (ON)}	V _{GS} =10V, I _D =500mA		1.2	3.5	Ω
		V _{GS} =5.0V, I _D =50mA		1.7	7.5	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz		20	50	pF
Output Capacitance	C _{OSS}			11	25	pF
Reverse Transfer Capacitance	C _{RSS}			4	5	pF
Turn-On Time	t _{ON}	V _{DD} =30V, R _L =150Ω I _D =200mA, V _{GS} =10V R _{GEN} =25Ω			20	nS
Turn-Off Time	t _{OFF}	V _{DD} =30V, R _L =25Ω I _D =200mA, V _{GS} =10V R _{GEN} =25Ω			20	nS
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =115mA (Note)		0.88	1.5	V
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				0.8	A
Maximum Continuous Drain-Source Diode Forward Current	I _S				115	mA

Note: Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2.0\%$

■ TEST CIRCUIT AND WAVEFORM

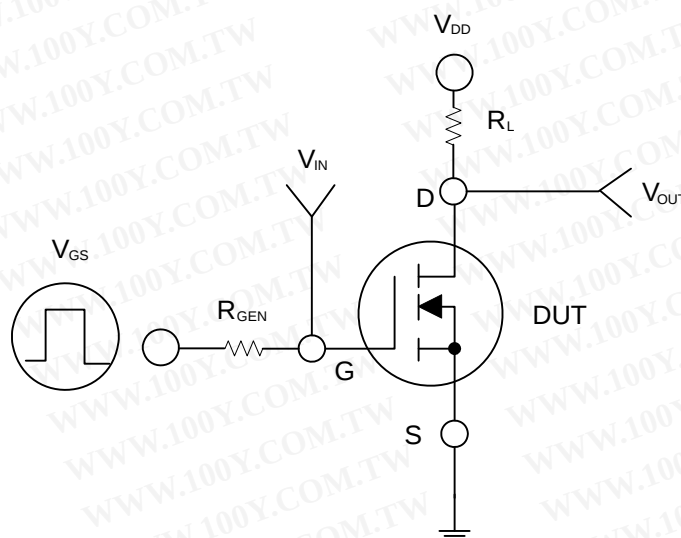


Figure 1

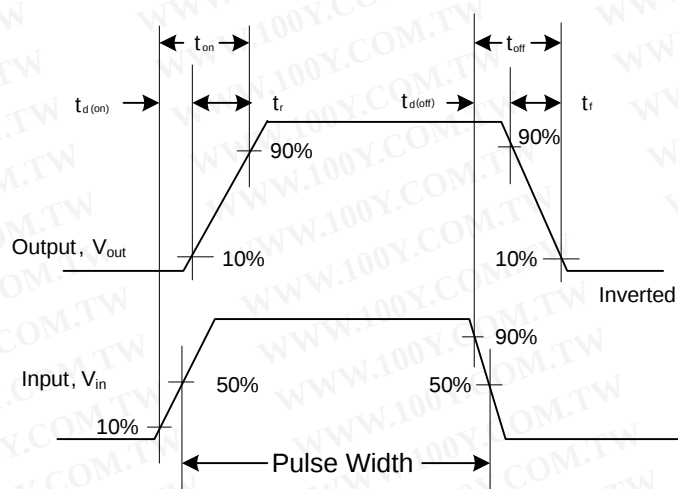
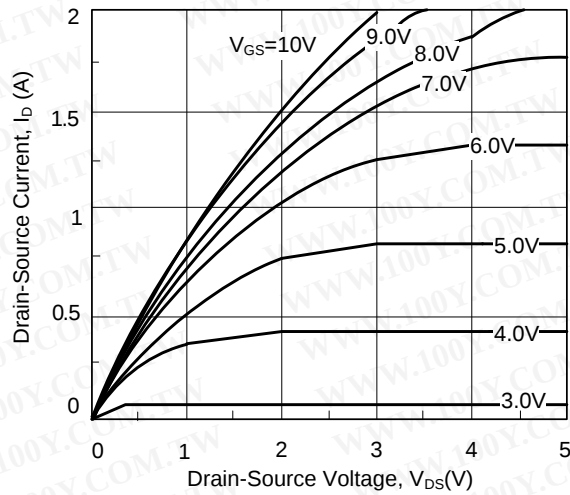


Figure 2. Switching Waveforms

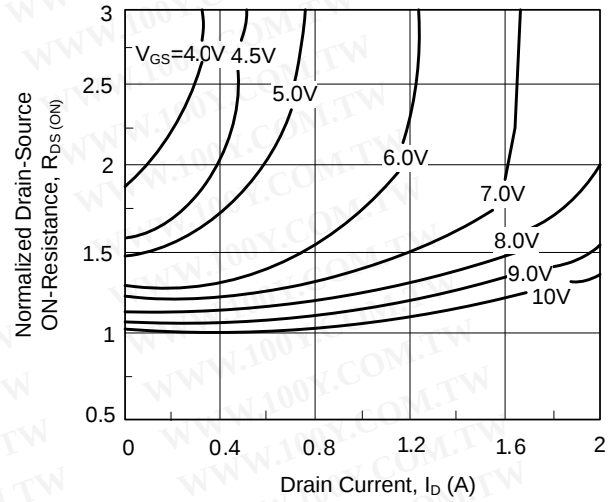
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■ TYPICAL CHARACTERISTICS

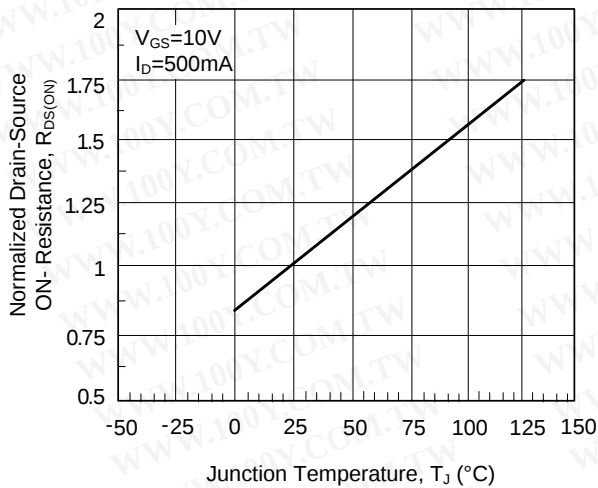
On-Resistance Characteristics



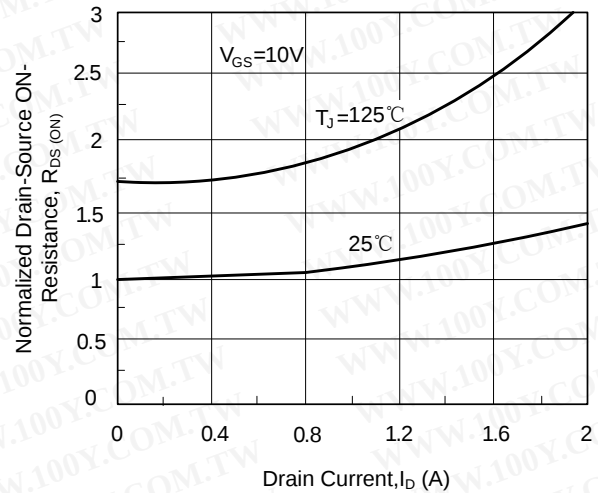
On-Resistance Variation with Gate Voltage and Drain Current



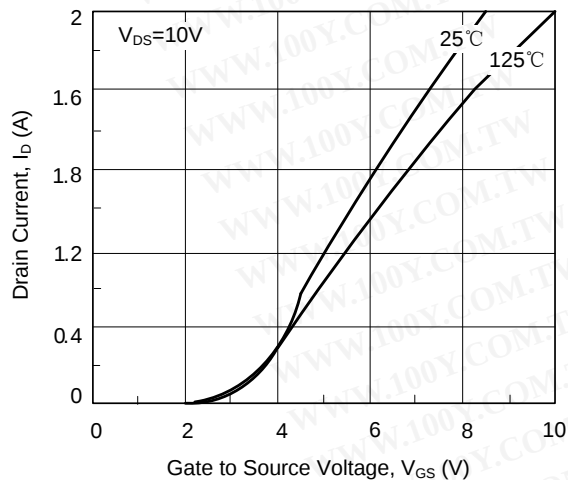
On-Resistance Variation with Temperature



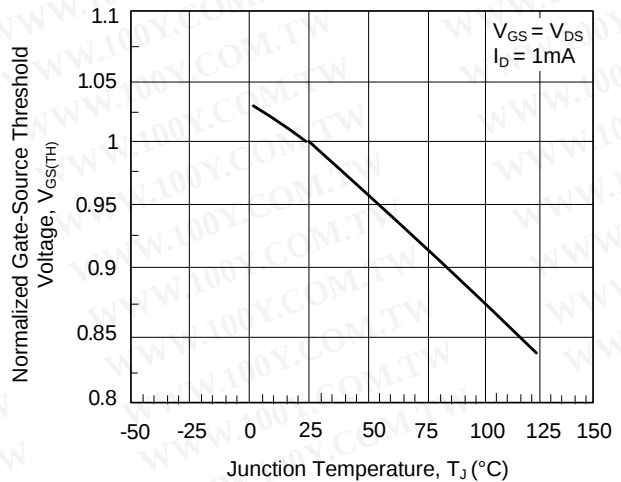
On-Resistance Variation with Drain Current and Temperature



Transfer Characteristics



Gate Threshold Variation with Temperature

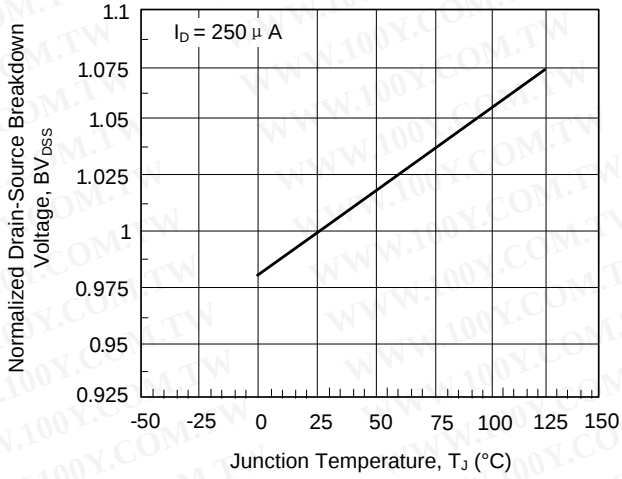


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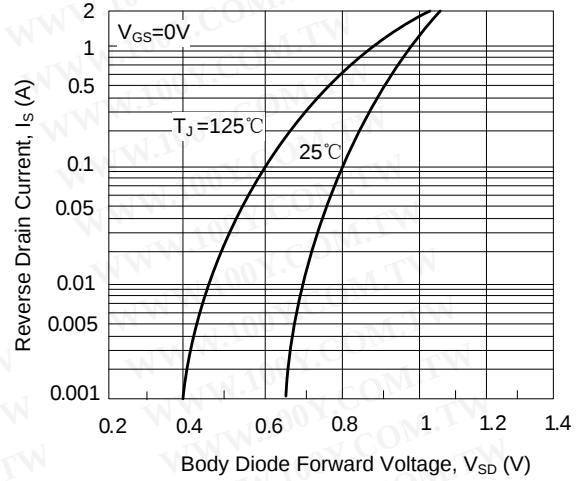
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TYPICAL CHARACTERISTICS (Cont.)

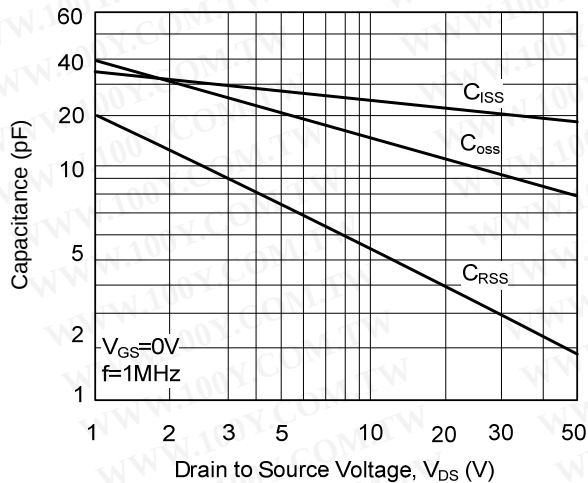
Breakdown Voltage Variation with Temperature



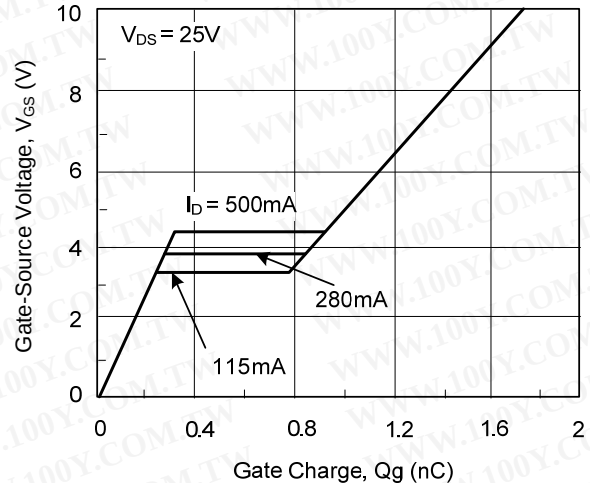
Body Diode Forward Voltage Variation with Temperature



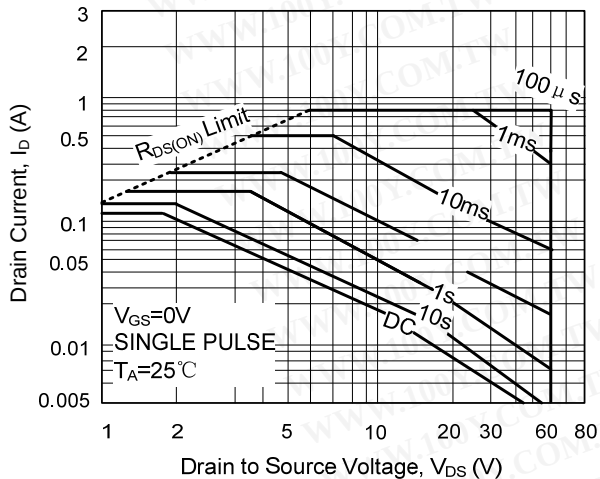
Capacitance Characteristics



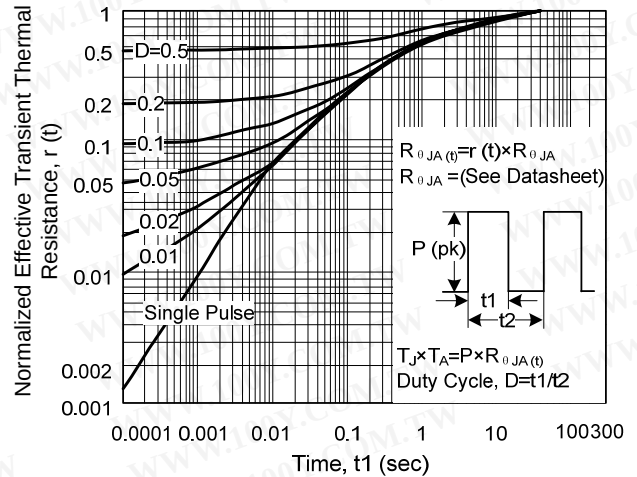
Gate Charge Characteristics



Maximum Safe Operating Area



Transient Thermal Response Curve



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